

MIP160, MIP162, MIP163, MIP164, MIP165, MIP166

Silicon MOS IC

■ Features

- Single chip IC with high breakdown voltage power MOS FET and CMOS control circuit
- Worldwide input (85 to 274VAC) possible
- Over-voltage protection at secondary section, pulse by pulse over-current protection, and intermittent operation timer at overload

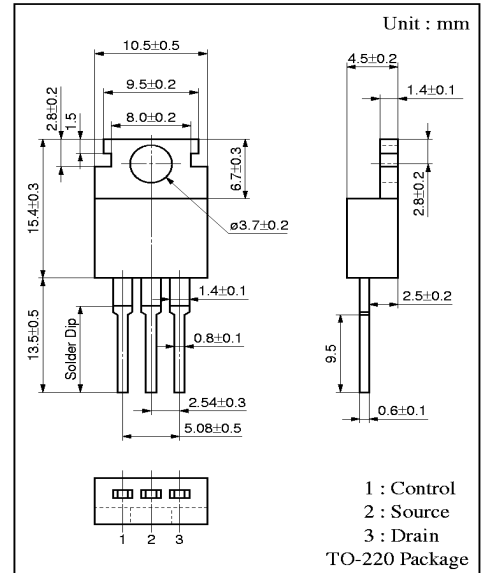
■ Applications

- Switching mode regulator (5 to 40W)
- AC adapter
- Battery charger

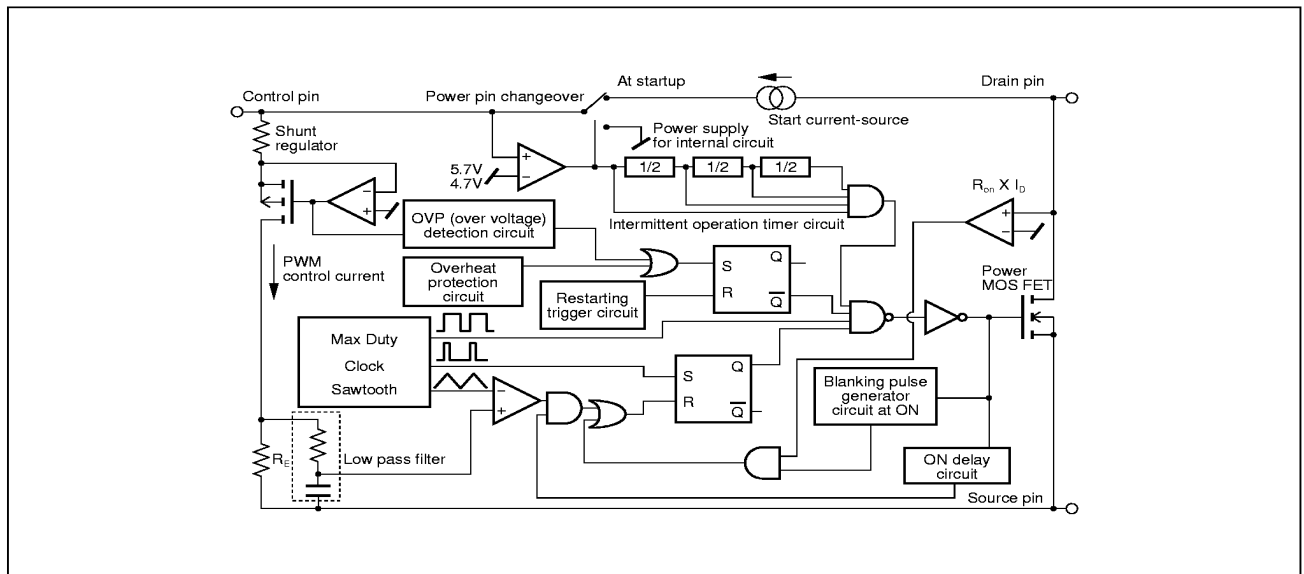
■ Absolute Maximum Ratings (Ta= 25°C)

Parameter	Symbol	Rating	Unit
Drain voltage	V _D	700	V
Control voltage	V _C	8	V
Output current	I _D	I _{LIMIT}	A
Control current	I _C	0.1	A
Allowable power dissipation	P _D	1.7/12.5 * 1	W
Operating ambient temperature	T _{opr}	- 20 to + 85	°C
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	- 55 to +150	°C

* 1 : T_C= 25°C



■ Block Diagram



■ Electrical Characteristics (T_c= 25± 2°C)

Parameter		Symbol	Condition	Min	Typ	Max	Unit	
Control function	Output frequency	f _{osc}	I _C = 4mA	90	100	110	kHz	
	Maximum duty cycle	MAXDC	I _C = 2mA	64	67	70	%	
	Minimum duty cycle	MINDC	I _C =10mA	1	2	3	%	
Start up	Control pin charge current	I _C	V _C = 0V	-2.4	-1.9	-1.2	mA	
			V _C = 5V	-2.0	-1.5	-0.8		
	Control pin voltage at startup	V _{C(ON)}		5.0	5.7	6.3	V	
	Control pin voltage at stop	V _{C(OFF)}		4.0	4.7	5.3	V	
	Start/stop hysteresis voltage	ΔV _C		0.5	1.0	1.5	V	
	Intermittent operation time-ratio	T _{SW} /T _{TIM}			5	8	%	
	Intermittent operation frequency	f _{TIM}		0.5	1.2	2.0	Hz	
Protection function	Over current protection/detection	I _{LIMIT}		0.415	0.5	0.585	A	
			MIP160		0.75	0.9		1.05
			MIP162		1.12	1.35		1.57
			MIP163		1.35	1.62		1.89
			MIP164		1.88	2.25		2.63
			MIP165		2.4	2.8		3.2
		Blanking width at ON	t _{on(BLK)}	I _C = 4mA		0.25		μs
		Over current protection delay time	t _{d(OCL)}	I _C = 4mA		0.1		μs
		Over current protection temperature	T _{OTP}	I _C = 4mA	130	140	150	°C
		Over voltage protection/detection current	I _{ovp}		25	45	75	mA
	Latch reset voltage	V _{C reset}		2.3	3.3	4.2	V	
Output	ON resistance	R _{DS(ON)}		0.1A		15	18	Ω
				0.3A		8.5	10	
				0.3A		5.8	6.7	
				0.5A		4.5	5.5	
				0.8A		3.0	3.8	
				1.0A		2.6	3.3	
		Drain pin leak current at OFF	I _{DSS}	V _{DS} = 650V, I _C = 4mA latch mode		0.5	0.9	mA
		Drain breakdown voltage	V _{DS}	I _C = 4mA, I _D = 0.25mA latch mode	700			V
		Rise time	t _r			0.1	0.2	μs
		Fall time	t _f			0.1	0.2	μs
Supply voltage	Minimum drain voltage	V _{D(MIN)}		36			V	
	Shunt regulator voltage	V _C	I _C = 4mA	5.5	5.8	6.1	V	
	Control pin discharge current	I _{CD1}	at output MOS operation	0.7	1.4	1.8	mA	
		I _{CD2}	at output MOS stop	0.5	0.8	1.1	mA	